

DATA SHEET

SA56606-XX CMOS system reset

Product data

2001 Jun 19

Supersedes data of 2001 Apr 24

File under Integrated Circuits, Standard Analog

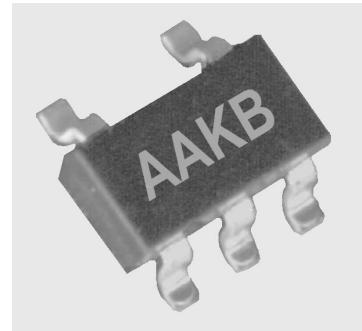
CMOS system reset

SA56606-XX

GENERAL DESCRIPTION

The SA56606-XX is a CMOS device designed to generate a reset signal for a variety of microprocessor and logic systems. Accurate reset signals are generated during momentary power interruptions or whenever power supply voltages sag to intolerable levels. An Open Drain output topology is incorporated for adaptability to a wide variety of logic and microprocessor applications. Several reset threshold versions of the device are available.

The SA56606-XX is available in the SOT23-5 surface mount package.



FEATURES

- 12 V_{DC} maximum operating voltage
- CMOS N-channel Open Drain output
- Offered in reset thresholds of 2.0, 2.7, 2.8, 2.9, 3.0, 3.1, 4.2, 4.3, 4.4, 4.5, 4.6, 4.7 V_{DC}
- Available in SOT23-5 surface mount package

APPLICATIONS

- Microcomputer systems
- Logic systems
- Battery monitoring systems
- Back-up power supply circuits
- Voltage detection circuits

SIMPLIFIED SYSTEM DIAGRAM

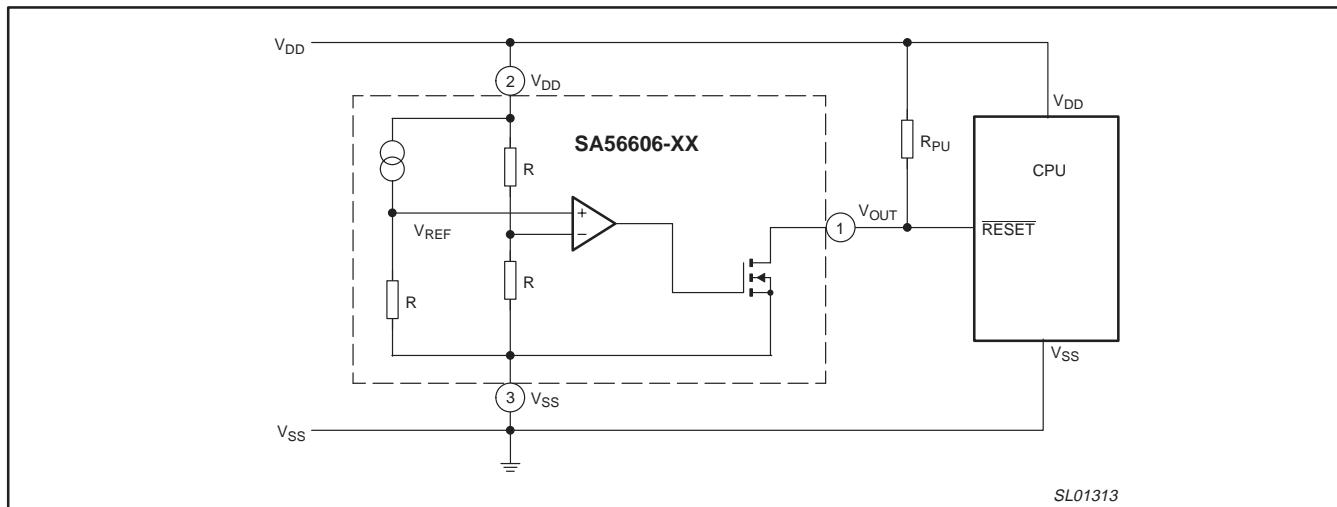


Figure 1. Simplified system diagram.

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ORDERING INFORMATION

TYPE NUMBER	PACKAGE		TEMPERATURE RANGE
	NAME	DESCRIPTION	
SA56606-XXGW	SOT23-5, SOT25, SO5	plastic small outline package; 5 leads (see dimensional drawing)	-40 to +85 °C

NOTE:

The device has twelve detection voltage options, indicated by the **XX** on the order code.

XX	DETECT VOLTAGE (Typical)
20	2.0 V
27	2.7 V
28	2.8 V
29	2.9 V
30	3.0 V
31	3.1 V
42	4.2 V
43	4.3 V
44	4.4 V
45	4.5 V
46	4.6 V
47	4.7 V

Part number marking

Each package is marked with a four letter code. The first three letters designate the product. The fourth letter, represented by 'x', is a date tracking code. For example, AAKB is device AAK (the SA56606-30 reset), produced in time period 'B'.

Part number	Marking
SA56606-20	AA F x
SA56606-27	AA G x
SA56606-28	AA H x
SA56606-29	AA J x
SA56606-30	AA K x
SA56606-31	AA L x
SA56606-42	AA M x
SA56606-43	AA N x
SA56606-44	AA P x
SA56606-45	AA R x
SA56606-46	AA S x
SA56606-47	AA T x

PIN CONFIGURATION

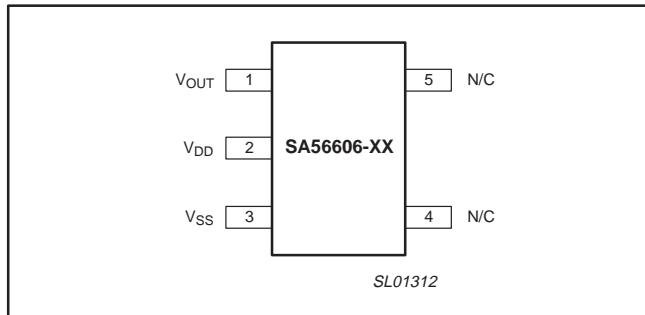


Figure 2. Pin configuration.

PIN DESCRIPTION

PIN	SYMBOL	DESCRIPTION
1	V_{OUT}	Reset High Output
2	V_{DD}	Positive Supply
3	V_{SS}	Ground. Negative Supply
4	N/C	No connection
5	N/C	No connection

MAXIMUM RATINGS

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V_{DD}	Power supply voltage	-0.3	12	V
V_{OUT}	Output voltage	-	$V_{SS} - 0.3$	V
I_{OUT}	Output current	-	50	mA
T_{oper}	Operating temperature	-40	85	°C
T_{stg}	Storage temperature	-40	125	°C
P	Power dissipation	-	150	mW

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DC ELECTRICAL CHARACTERISTICS

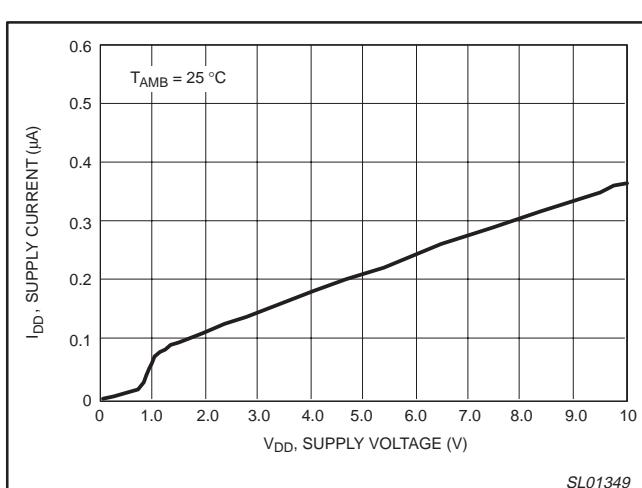
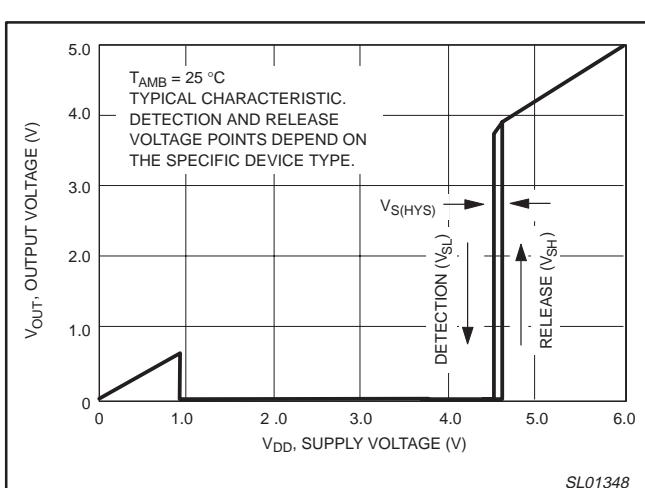
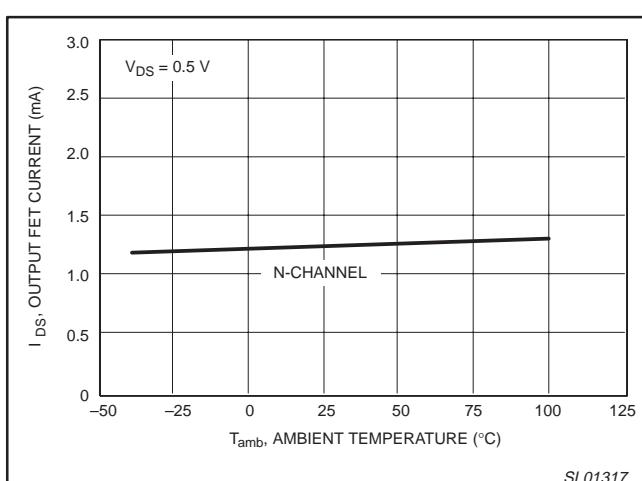
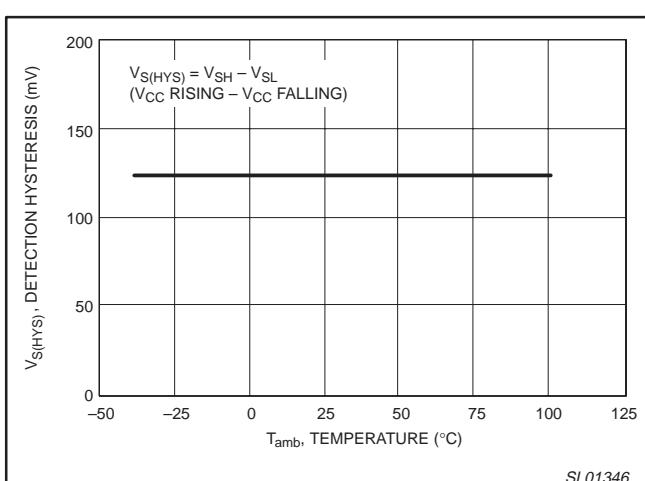
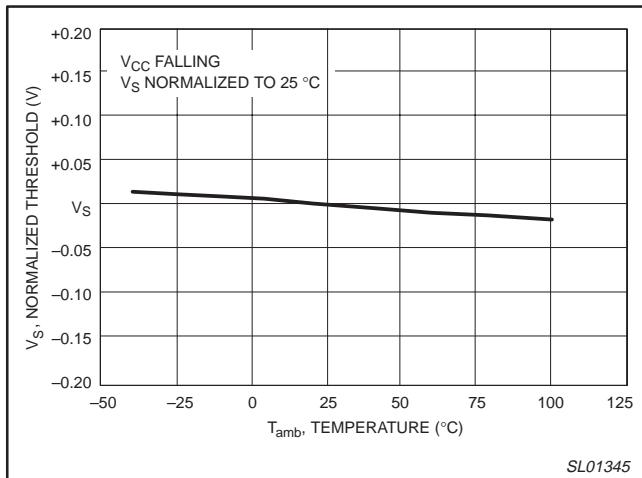
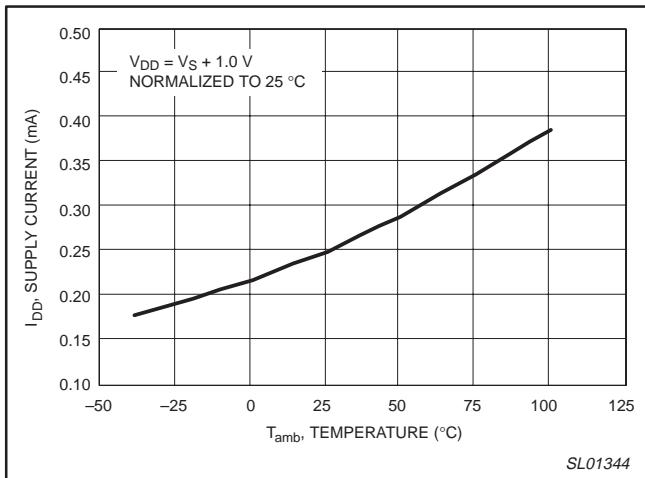
Characteristics measured with $T_{amb} = 25^\circ\text{C}$, unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TEST CIRCUIT	MIN.	TYP.	MAX.	UNIT
V_S	Reset detection threshold		1 Fig. 17	$V_S - 2\%$	V_S	$V_S + 2\%$	V
ΔV_S	Hysteresis	$V_{DD} = 0 \text{ V} \rightarrow V_S + 1.0 \text{ V} \rightarrow 0 \text{ V}$		$V_S \times 0.03$	$V_S \times 0.05$	$V_S \times 0.08$	V
$V_S/\Delta T$	Threshold voltage temperature coefficient	$-40^\circ\text{C} \leq T_{amb} \leq +85^\circ\text{C}$		–	± 0.01	–	$^\circ\text{C}$
I_{CC}	Supply current	$V_{DD} = V_S + 1.0 \text{ V}$		–	0.25	1.0	μA
I_{OH}	I_{DS} leakage current when OFF	$V_{DD} = V_{DS} = 10 \text{ V}$	2 Fig. 18	–	–	0.1	μA
I_{DS1}	N-channel I_{DS} output sink current 1	$V_{DS} = 0.5 \text{ V}; V_{DD} = 1.2 \text{ V}$		–0.23	–1.4	–	mA
I_{DS2}	N-channel I_{DS} output sink current 2 (for $V_S > 2.6 \text{ V}$)	$V_{DS} = 0.5 \text{ V}; V_{DD} = 2.4 \text{ V}$		–1.6	–8.3	–	mA
I_{DS3}	N-channel I_{DS} output sink current 3 (for $V_S > 3.9 \text{ V}$)	$V_{DS} = 0.5 \text{ V}; V_{DD} = 3.6 \text{ V}$		–3.2	–14.7	–	mA

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TYPICAL PERFORMANCE CURVES



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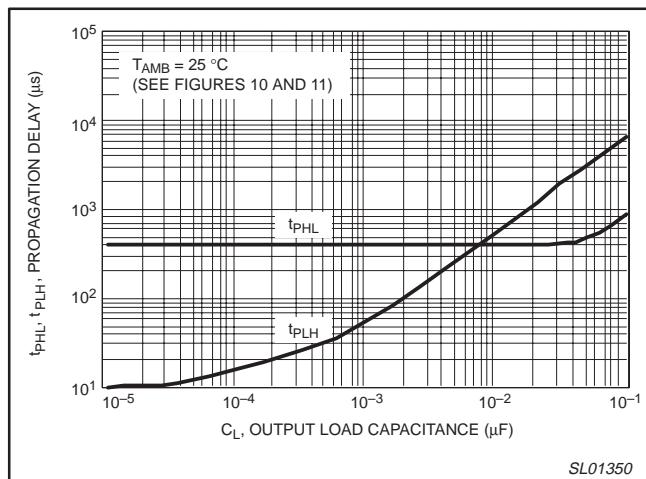


Figure 9. Propagation delay versus output load C

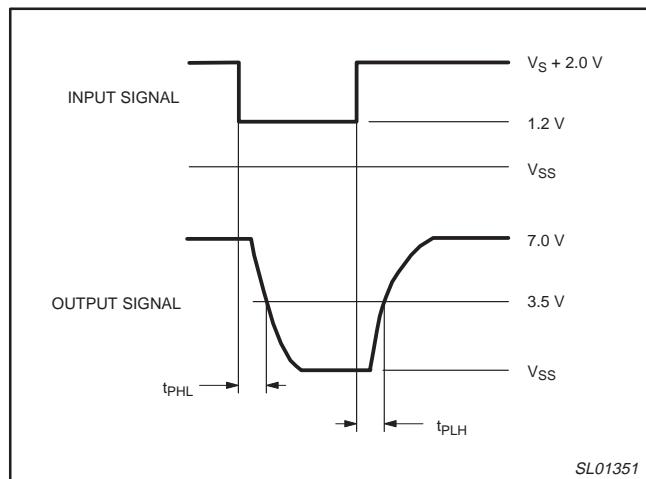


Figure 10. Propagation delay measurements

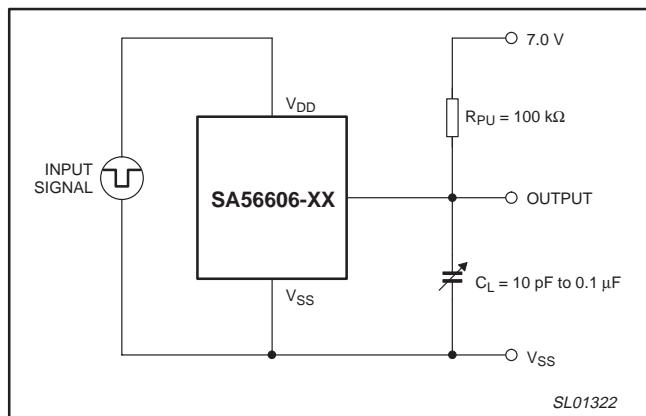


Figure 11. Propagation delay measurement circuit

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TECHNICAL DESCRIPTION

The SA56606-XX is a CMOS device designed to provide power source monitoring and a system reset function in the event the supply voltage sags below an acceptable level for the system to reliably operate. The device is designed to generate a compatible reset signal for a wide variety of microprocessor and logic systems. The SA56606 can operate at voltages up to 12 volts. The series includes several versions providing precision threshold voltage reset values of 2.0, 2.7, 2.8, 2.9, 3.0, 3.1, 4.2, 4.6 and 4.7 V. The reset threshold incorporates a typical hysteresis of $(V_S \times 0.05)$ volts to prevent erratic resets from being generated.

The output of the SA56606 utilizes a low side open drain topology, which requires an external pull-up resistor (R_{PU}) to the V_{DD} power source. Although this may be regarded as a disadvantage, it is an advantage in many sensitive applications because the open drain output cannot source reset current to a microprocessor when both are operated from a common supply. For this reason the SA56606 offers a safe inter-connect to a wide variety of microprocessors.

The SA56606 operates at very low supply currents, typically 0.25 μ A, while offering a high precision of threshold detection ($\pm 2\%$). Figure 12 is a functional block diagram of the SA56606. The internal reference source voltage (V_{REF}) is typically 0.8 V over the operating temperature range. The reference voltage is connected to the non-inverting input of the threshold comparator, while the inverting input monitors the supply voltage through a resistor divider network made up of R_1 , R_2 , and R_3 . The output of the threshold comparator drives the output Open Drain N-Channel FET of the device TR_1 . When the supply voltage sags to the threshold detection voltage, the resistor divider network supplies a voltage to the inverting input of the threshold comparator, which is less than that of V_{REF} , causing the output of the comparator to go to a HIGH output state. This causes the low side N-Channel FET to be active ON, pulling its drain voltage to a LOW state. The device adheres to a true input/output logic protocol: the output goes LOW when input is LOW (below threshold) and output goes HIGH when input is HIGH (above threshold).

The low side N-Channel FET (TR_2) establishes threshold hysteresis by turning ON whenever the threshold comparator's output goes to a HIGH state (when V_{DD} sags to or below the threshold level). TR_2 's turning ON causes additional current to flow through resistors R_1 and R_2 , causing the inverting input of the threshold comparator to be pulled even lower. For the comparator to reverse its output polarity and turn OFF TR_2 , the V_{DD} source voltage must overcome this additional pull-down voltage present on the comparator's inverting input. The differential voltage required to do this establishes the hysteresis voltage of the sensed threshold voltage. Typically it is $(V_S \times 0.05)$ volts.

When the V_{DD} voltage sags, and is at or below the Detection Threshold (V_{SL}), the device will assert a Reset LOW output at or very near ground potential. As the V_{DD} voltage rises from $(V_{DD} < V_{SL})$ to V_{SH} or higher, the Reset is released and the output follows V_{DD} . Conversely, decreases in V_{DD} from $(V_{DD} > V_{SL})$ to V_{SL} or lower cause the output to be pulled to ground.

$$\text{Hysteresis Voltage} = \text{Release Voltage} - \text{Detection Threshold Voltage}$$

$$V_{HYS} = V_{SH} - V_{SL}$$

where:

$$V_{SH} = V_{SL} + V_{HYS} \equiv V_{REF}(R_1 + R_2) / R_2$$

$$V_{SL} = V_{REF}(R_1 + R_2 + R_3) / (R_2 + R_3)$$

When V_{DD} drops to levels below the minimum operating voltage, typically less than 0.95 volts, the output is undefined and output reset LOW assertion is not guaranteed. At this level of V_{DD} the output will try to rise to V_{DD} .

The V_{REF} voltage is typically 0.8 V. The devices are fabricated using a high resistance CMOS process and utilize high resistance R_1 , R_2 , and R_3 values requiring very small amounts of current. This combination achieves very efficient low power performance over the full operating temperature.

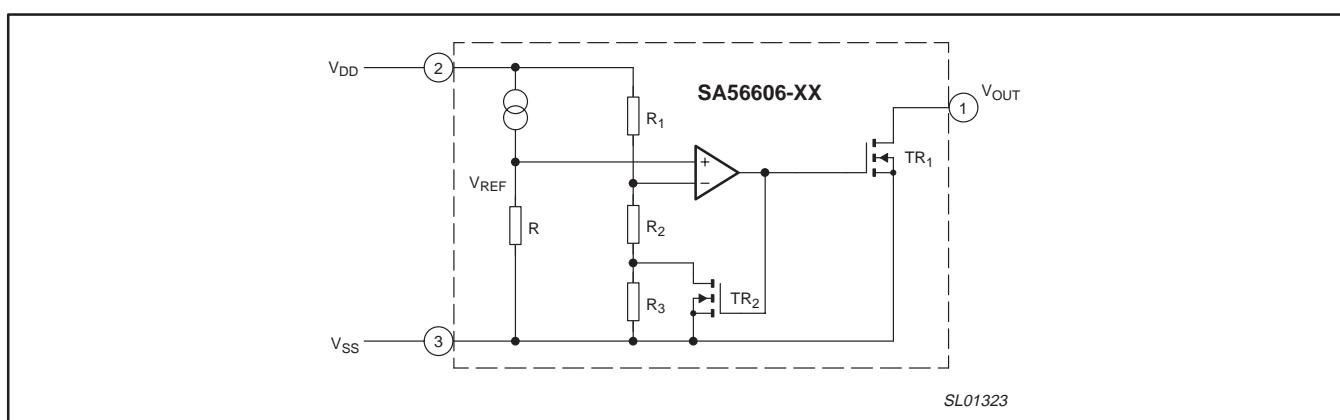


Figure 12. Functional diagram.

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Timing diagram

The timing diagram shown in Figure 13 depicts the operation of the device. Letters A–J on the TIME axis indicate specific events.

A: At 'A', V_{DD} begins to increase. Also the V_{OUT} voltage initially increases but abruptly decreases when V_{DD} reaches the level (approximately 0.8 V) that activates the internal bias circuitry and RESET is asserted.

B: At 'B', V_{DD} reaches the threshold level of V_{SH} . At this point the device releases the hold on the V_{OUT} reset. The Reset output V_{OUT} tracks V_{DD} as it rises above V_{SH} (assuming the reset pull-up resistor R_{PU} is connected to V_{DD}). In a microprocessor based system these events release the reset from the microprocessor, allowing the microprocessor to function normally.

C–D: At 'C', V_{DD} begins to fall, causing V_{OUT} to follow. V_{DD} continues to fall until the V_{SL} undervoltage detection threshold is reached at 'D'. This causes a reset signal to be generated (V_{OUT} Reset goes LOW).

D–E: Between 'D' and 'E', V_{DD} starts rising.

E: At 'E', V_{DD} rises to the V_{SH} . Once again, the device releases the hold on the V_{OUT} reset. The Reset output V_{OUT} tracks V_{DD} as it rises above V_{SH} .

F–G: At 'F', V_{DD} is above the upper threshold and begins to fall, causing V_{OUT} to follow it. As long as V_{DD} remains above the V_{SH} , no reset signal will be triggered. Before V_{DD} falls to the V_{SH} , it begins to rise, causing V_{OUT} to follow it. At 'G', V_{DD} returns to normal.

H: At event 'H' V_{DD} falls until the V_{SL} undervoltage detection threshold point is reached. At this level, a \overline{RESET} signal is generated and V_{OUT} goes LOW.

J: At 'J' the V_{DD} voltage has decreased until normal internal circuit bias is unable to maintain a V_{OUT} reset. As a result, V_{DD} may rise to less than 0.8 V. As V_{DD} decreases further, V_{OUT} reset also decreases to zero.

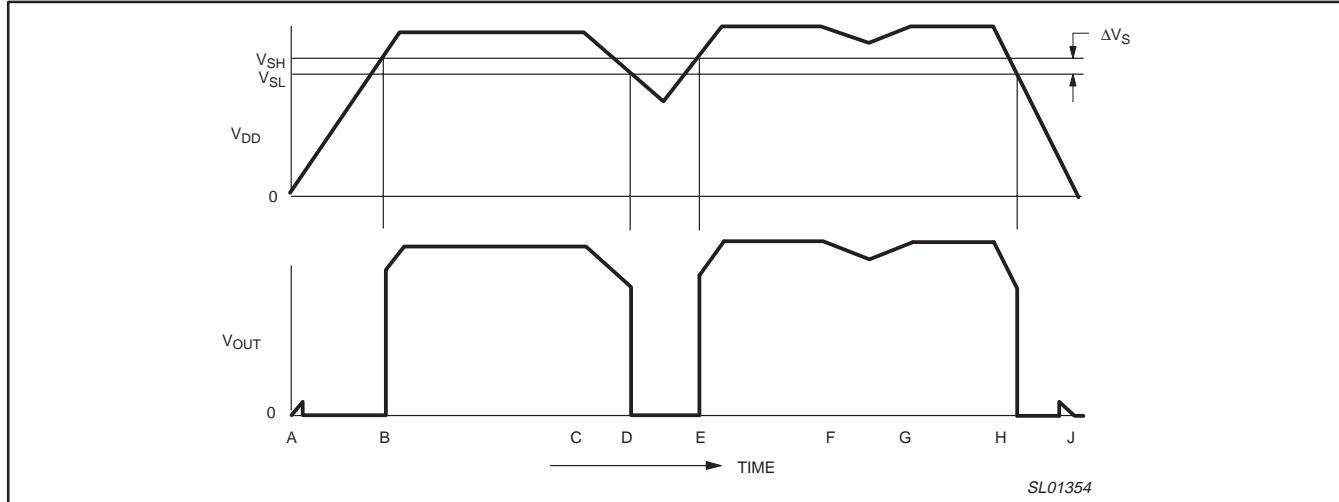


Figure 13. Timing diagram.

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Application information

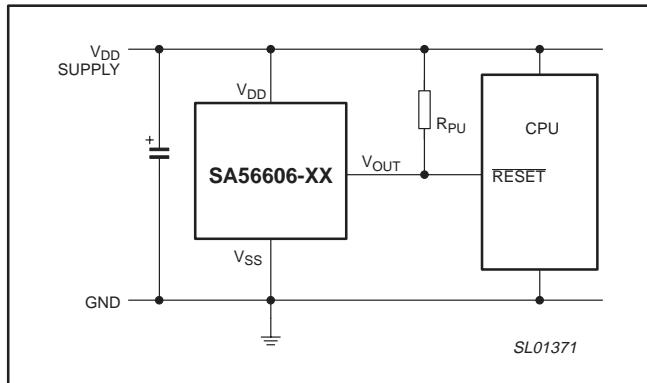


Figure 14. Conventional reset application.

The Power ON Reset Circuit shown in Figure 15 is an example of how to obtain a stable reset condition upon power-up. If the power supply voltage rises abruptly, the $RESET$ may go HIGH momentarily when V_{DD} is below the minimum operating voltage (0.95 V). To overcome this, a resistor (R) is placed between positive supply and the V_{DD} pin with a capacitor from the V_{DD} pin to ground.

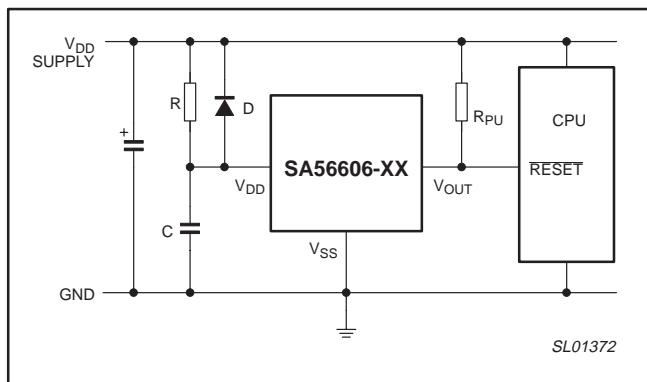


Figure 15. Power ON reset circuit.

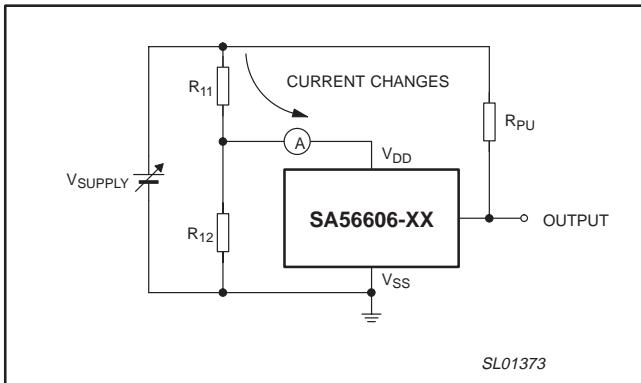


Figure 16. High impedance supply operating problems.

Significant voltage variations of V_{DD} may occur when the device is operated from high impedance power sources. When the device asserts or releases a reset, V_{DD} variations are produced as a result of the voltage drop developed across R_{11} due to the current variations through the resistor R_{11} (representing the supply impedance). If the V_{DD} variations are large, such that they exceed the Detection Hysteresis, the output of the device can oscillate from a HIGH state to a LOW state. The user should avoid using high impedance V_{DD} sources to prevent such situations.

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Test circuits

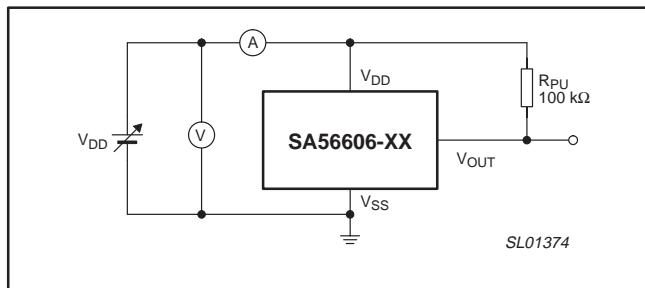


Figure 17. Test circuit 1.

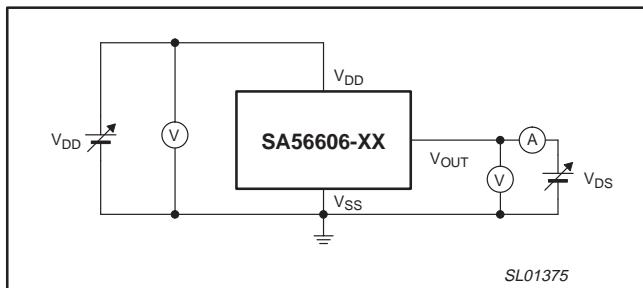


Figure 18. Test circuit 2.

PACKING METHOD

The SA56606-XX is packed in reels, as shown in Figure 19.

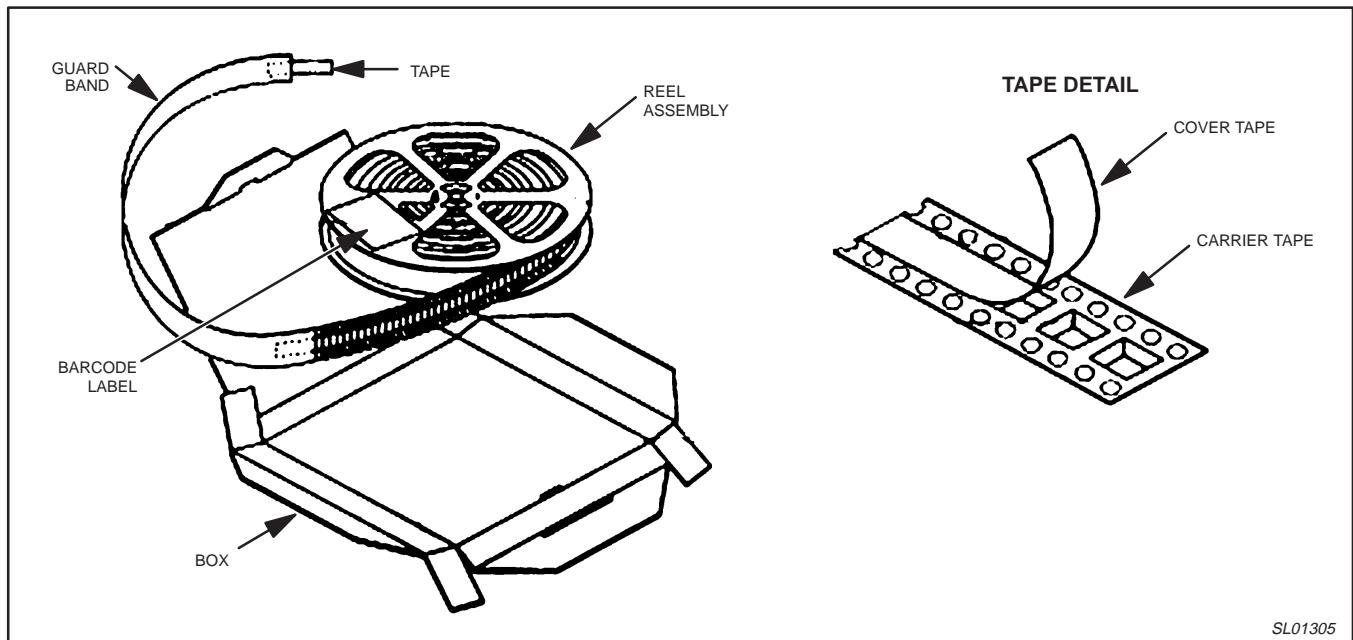
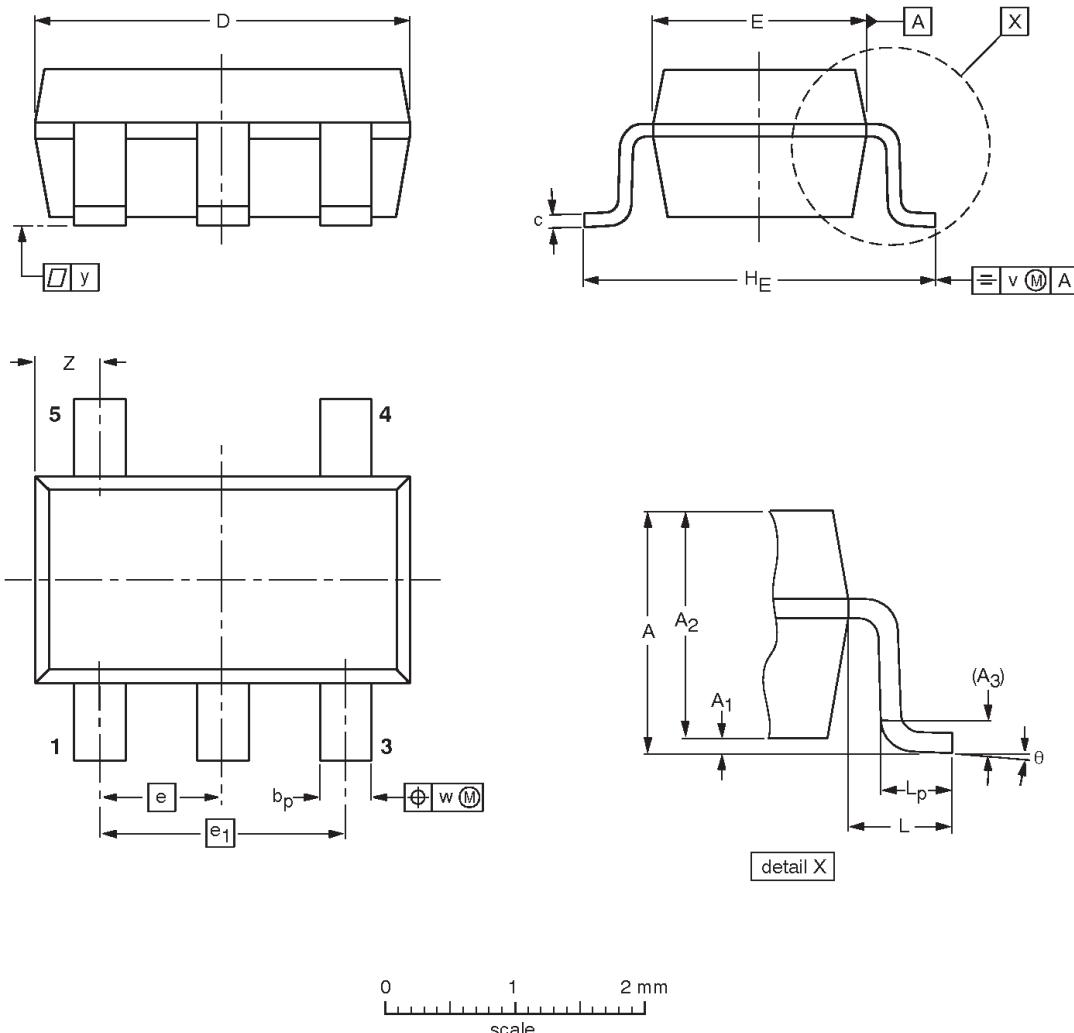


Figure 19. Tape and reel packing method

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SOT23-5: plastic small outline package; 5 leads; body width 1.5 mm



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽¹⁾	e	e ₁	H _E	L	L _p		y		θ
mm	1.35 0.15	0.05 1.0	1.2	0.025	0.55 0.41	0.22 0.08	3.00 2.70	1.70 1.50	0.95	1.90	3.00 2.60	0.60	0.55 0.35		0.1		8° 0°

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES		
	IEC	JEDEC	EIAJ
		MO-178	

Data sheet status

Data sheet status ^[1]	Product status ^[2]	Definitions
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

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